ABSTRACT OF THE DISCLOSURE

METHOD FOR FABRICATING III-V COMPOUND SEMICONDUCTOR

A method for fabricating a III-V Group compound semiconductor comprising a step of epitaxially growing on an $Al_xGa_{1-x}As$ layer of lower Al content an $Al_xGa_{1-x}As$ layer of higher Al content, in which step a growth rate of the $Al_xGa_{1-x}As$ layer of higher Al content is made slower than a growth rate of the $Al_xGa_{1-x}As$ layer of lower Al content, thereby effectively inhibiting the occurrence of starting points of abnormal growth at the interface between the two layers.